



Coventor platform for MEMS design, – from device design and process development to system optimization

Chris Welham Application Engineering Manager Coventor Paris



## **Overview of Coventor**

# Founded in 1996 with a focus on software for MEMS Design

- Management team from MEMS and EDA
- Validated tools and library across a broad range
  - of designs and applications

### **Initial products for MEMS 'experts'**

- Device design, modeling, simulation
- Process development

# Established proven track record with MEMS market leaders

- Top tier MEMS device makers and specialized manufacturers
- 11 of top 15 MEMS companies\* use Coventor

\*Source: Yole Development (Feb. 2010): Top 15 MEMS companies = 80% of MEMS market



### **Coventor's Mission**

### Enable Our Customers to Grow Their MEMS Business

- Providing Essential Design Automation Software
- Setting the Standards for MEMS Design Methodology
- Partnering for Success

### COVENTOR

### **A Diversity of Customers**









# Simulation of Complete Product

MEMS-based products are becoming more integrated



Increasing integration requires more verification by simulation

- More difficult or impossible to test individual components
- More chance of design errors in interconnect
- > More likelihood of undesirable coupling between components
- More sensitive to signal integrity and parasitics

Simulations must include more of the system

### It is no longer sufficient to simulate individual system blocks



# **Overview of CoventorTools**





## Overview of CoventorTools



### MEMS+

 MEMS behavioral modeling environment





# MEMS+System & IC Challenge

- System, IC and layout designers require a MEMS component for their design environment
- No standard, automated methodology across the industry
- Disconnect between MEMS, System and IC design flows leads to long development cycles and high costs and minimal design reuse





# Coventor MEMS+ for Matlab Simulink



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# Coventor MEMS+ for Cadence Virtuoso





 The MEMS+ component library is build on top of three different mechanical model families





## Add-on Models





MEMS+ is built on a comprehensive model library

- Beams & Suspensions (FEA Elements Bernoulli Beam Theory)
- Plates (FEA Elements Flexible MITC Plate Theory)
- Sensing Electrodes, (Conformal Mapping Theory)
- Comb Finger Drives (Conformal Mapping Theory)



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# Model Verification Example

 All our electrostatic models are carefully verified against our BEM solver



BEM mesh model used as reference

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Horizontal Force (horizontal overlap 40 um)



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# *MEMS+* Design Examples 1

 MEMS+ builds on Coventor's parametric model library which has been proven on real-world designs...



#### Display Devices

**PZE** Actuated Mirror









# *MEMS+* Design Examples 2

 MEMS + builds on Coventor's parametric model library which has been proven on real-world designs...

Gyros (Angular Rate Sensors)



Capactive/PZE Microphone







Accelerometers



## Overview of CoventorTools



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# Overview of DESIGNER





# DESIGNER<sup>™</sup> Layout Editor

# Has standard layout editor functionality, plus MEMS-specific features

- Enter true curves (arcs, circles, splines) for efficient 3D solid modeling
- Save time by using hierarchical layout cells
- Parametric MEMS layout cell generators
- Import standard layout formats (GDS2, DXF)

## Verify design before tape out

- Layer browser shows layer-to-mask mapping
- Built-in design rule checks
- Mask Viewer allows users see the masks exactly as they will be manufactured





# DESIGNER<sup>™</sup> Process Editor

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Company Kon silicon etchis used to form a 25µm deep tenchin the silicon substrate in the areas						E PostalMUMPs
standard	STANDARD					
foundry processes						li.



# DESIGNER<sup>TM</sup> Solid Modeler

- 3D Solid Model Builder
  - Employs the 2D layout and fabrication process description to automatically build 3D models (ACIS SAT format)
  - Emulates real foundry steps, such as etching through multiple layers or partial backside etching









# DESIGNER™ Preprocessor

### Optimized for MEMs layers

### Features include

- Cross-section planes
- Solid model partitioning & transforms
- Automatic layer merging to assure conformal meshes
- Part and face labeling for BCs
- Mesh generation
- Mesh quality checks





Tree expands to show only named or highlighted entities Same plane can be used as x-section, partition or symmetry.

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# **DESIGNER<sup>™</sup> Meshing**

# Choose from 5 optimized mesh generators that are ideal for MEMS solid models

- 1. Manhattan bricks (hexes) for near orthogonal geometry
- 2. Extruded bricks for multi-layered non-orthogonal geometry (choose from 3 algorithms)
- 3. Mapped meshing for 6-sided volumes
- 4. Tetrahedrals meshing for arbitrary shapes
- 5. Surface meshing (triangles and quadrilaterals) for BEM

Local refinement controls on all model entities (layers, parts, faces, edges, vertices)

Mesh quality checks

- Easy to read reports
- Highlighted display of "bad" elements

Import/export ANSYS meshes





# Overview of ANALYZER™

- Comprehensive suite of 3D field solvers for MEMS
- Coventor solvers for thermo-mechanics, electrostatics, damping, piezo-resistance, piezoelectric effect
  - Hybrid FEM/BEM approach to coupled electromechanics
  - Gas damping, Anchor Damping, TED
- Simulation management
- Versatile results visualization





# Overview of ANALYZER™

### 1. Comprehensive suite of 3D field solvers

Multi-physics with multi-core and 64-bit support

		MEMS 🍐 O Microfluidics
дη	MemElectro	(electrostatic and electroquasistatic)
իհ	MemElectro	(electrostatic and electroquasistatic)
Ц	MemMech	(mechanical, thermomechanical and piezoelectric)
K	CoSolveEM	(coupled electromechanical - static)
₽¥	HarmonicEM	(coupled electromechanical - frequency domain)
+ -	MemPZR	(piezoresistance)
]00	MemHenry	(electrical inductance and resistance)
ᆊ″	SpringMM	(electrostatic, mechanical or electromechanical)
Ļ	DampingMM	(squeezed-, slide-film or free-space fluid damping)
凎	InertiaMM	(proof mass or plate inertia)

### 2. Simulation management

#### Relational database

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#### Visualizer

### 3. Postprocessing

# Convenient pre-defined tables and custom queries

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2	6.375334E08	5.350629E-13	0			
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4	6.380271E08	9.855608E-13	0			
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# CoventorWare Compatibility





# MEMS Examples in ANALYZER<sup>™</sup>



Accelerometer (Coupled Electro-Mechanics, Gas Damping)



**FBAR** (Piezoelectric and Mechanical Effects)



**RF Switch** (Coupled Electro-Mechanics, Gas Damping)



# ANALYZER<sup>™</sup> Examples MEMS





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# **Energy Harvester**

### Experimental Validation of Aluminum Nitride Energy Harvester Model with Power Transfer Circuit

S. Matova1, D. Hohlfeld1, R. van Schaijk1, C. J. Welham2, S. Rouvillois2 1 IMEC / Holst Centre, The Netherlands,

2Coventor, France





# ANALYZER<sup>™</sup> Examples MEMS





### Resistive Bolometer



100nW power absorbed by the detector: temperature gradient in the pixel is simulated in vacuum at temperature of 300 K

### **Diode Bolometer**





# Overview of CoventorTools

Material Properties Database and Process Editor

SEMulator3D Virtual prototyping





# Coventor is the leader in MEMS design automation software

Applying our technology to modeling MEMS and semiconductor processes in 3-D



# What is Virtual Fabrication?





# What is SEMulator3D

### A modeling tool used by leading MEMS and semiconductor fabs

### **GDSII** Layout



### **Process Description**



### 3D Modeling Engine

builds voxel models by applying a sequence of primitive operations



Voxels are 3D pixels

Customizable to any process technology

### Visualization







SEMulator3D follows a process "recipe" to emulate the fabrication sequence step-bystep:

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- Process recipe is composed of primitives from a standard library
- Primitive steps can be configured (calibrated) to match fab
- □ Input is *parameterized*
- Parameters are *geometric*; process setup is easy and fast

SEMulator3D can model **any** process technology.

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SEMulator3D Process Editor

## SEMulator3D Library of Standard Process Steps

- ✓ Conformal deposits
  CVD, PECVD, HDPCVD, etc
- ✓ Directional deposits
  Evaporation, sputtering
- ✓ Wet etches
  Including selectivity

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- ✓ Dry etches
  Plasma-based etches, RIE,
  DRIE, etc
- ✓ Growth
  - Oxide growth Epitaxy (some) Salicide Electroplate
- ✓ Miscellaneous
  СМР
  Lift-Off
  OOO "Евроинтех" 2012








## **Powerful 3D Visualization**

#### With the SEMulator3D Visualizer, you can



MEMS Motor using Metal MUMPS process

- □ Interact with a 3-D view
- Create and animate dimensionally accurate cross sections
- Color by material or by electrical connectivity
- Hide/show materials or electrical nets
- Take measurements
- Exaggerate scale in x,y or z
- Capture 3-D images
- Animate the fabrication steps

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## Example: MEMS DLP Mirror







DLP Process Sequence (above) and release etch (below).







DLP mirror based on a design by Texas Instruments. Note accurate representation of tether attachments!



## Example: SiGe Accelerometer





Figure 3: SEM view of the fabricated poly-SiGe lateral



#### A COMB BASED IN-PLANE SIGE CAPACITIVE ACCELEROMETER FOR ABOVE-IC INTEGRATION

L. Wen<sup>1</sup>, K. Wouters<sup>1</sup>, L. Haspeslagh<sup>2</sup>, A. Witvrouw<sup>2</sup>, R. Puers<sup>1</sup> <sup>1</sup>ESAT-MICAS, Katholieke Universiteit Leuven, Leuven, Belgium <sup>2</sup>IMEC, Kapeldreef 75, Leuven, Belgium +





## *Stopper* for SiGe Accelerometer



Figure 6: SEM view over the positioning of the shock protectors of the fabricated poly-SiGe lateral capacitive accelerome-OOQer"Евроинтех" 2012



## **Demo IMEC's SiGe**





## Who needs Virtual Fabrication

#### Process Development

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- Model the full fabrication sequence
- Prototype process changes before implementing them
- Predict process problems
- □ Save wafers (\$\$\$) and time

#### Foundry Services

- MEMS Design validation before fabrication
- Communication with customers

#### **MEMS** Designers

- Test manufacturability before tapeout
- Silicon-accurate models for FEM simulation
- Communication with fab

#### Process Documentation & Training

Add realistic 3D graphics for more effective documentation







## **Design Validation**

## Foundry Service companies use SEMulator3D to:

- Communicate design and process information with customers.
- □ Validate designs before fabrication.
- □ Efficiently model any design changes.
- □ Analyze and improve yield.
- Allow customers to build 3D models with SEMulator3D via PDK.





"Emulation also gives engineers the ability to do virtual test runs to verify that a device design is compatible with the manufacturing process, and that the 3D result is as expected. Moreover, design mistakes and shortcomings can be identified, even if they are compatible with 2D layout rules."



"The benefits of visualizing accurate 3-D virtual MEMS prototypes include increased probability of achieving first-time success by minimizing analysis errors, increased design efficiency by identifying process errors early, avoiding undesired effects that would have reduced yield, and more efficient communication between design engineers and outside groups."

## Baolab – Design review for PolyMUMPS with SEMulator3D

"We have now established a strict submission procedure within Baolab for all the foundry runs, and one imperative step is to simulate the whole die micromachining process using SEMulator3D and to visualize the 3D result using the mechanical coloring scheme, and this must be included in the final report."



Green indicates Oxide not removed despite non-violation of design rules



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## SEMulator3D Geometry Export

### SEMulator3D Reader

- An open version of SEMulator3D Viewer that anyone can download from Coventor's website
- SEMulator3D users can distribute 3D models to anyone.
- □ Encourage your prospects to try it out!



#### Mesh Generation

- SEMulator3D Meshing creates accurate surface and volume meshes for simulation:
  - Thermal
  - Mechanical stress/strain
  - Diffusion
  - Electrical parasitics
  - Multi-Physics (MEMS)
- SEMulator3D meshes can be used with CoventorWare Analyzer and 3rd-party solvers

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## **Design Kits**

Design your MEMS in stable well-known manufacturing processes using CoventorWare development platform

#### Data available:

- Specific material property databases
- Library of foundry specific process emulation files
- Layout template file incl. DRC
- Case studies and tutorials



## COVENTOR

## Library of Standard Foundry Processes

- **DALSA** post-processing on CMOS
- **IMEPKU Polysilicon**
- **PolyMUMPS 3-Layer Polysilicon Surface**
- SOIMUMPS SOI
- **MetalMUMPS Electroplating**
- Tronics 60µm SOI-HARM epitaxial SOI
- MultiMEMS Piezoresistive Bulk
- SINTEF MOVEMEMS PZT (beta)









VENTED CAVIT



## **Overview of CoventorTools**





## **Overview of CoventorTools**



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## Solution for MEMS Resonator Design and Integration

## MEMS Resonators for quartz replacement or RF applications

Electromechanical

• Piezoelectric

#### IEEE JOURNAL OF SOLID-STATE CIRCUITS, VOL. 39, NO. 12, DECEMBER 2004

#### Series-Resonant VHF Micromechanical Resonator Reference Oscillators

Yu-Wei Lin, Student Member, IEEE, Seungbae Lee, Student Member, IEEE, Sheng-Shian Li, Student Member, IEEE, Yuan Xie, Student Member, IEEE, Zeying Ren, Member, IEEE, and Clark T.-C. Nguyen, Senior Member, IEEE



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## **Specification Sheet**

## COVENTOR

#### **Electrical Characteristics**

Parameter	Symbol	Min.	Тур.	Max.	Unit	Condition	
Output Frequency Range	f	1	-	110	MHz		
Frequency Stability	F_stab	-20	-	+20	PPM	Inclusive of: Initial stability, operating temperature, rated pov	
		-25	-	+25	PPM	supply voltage change, load change, shock and vibration.	
	-	-30	-	+30	PPM	± 20 PPM available in extended commercial	
		-50	-	+50	PPM	temperature only	
Aging	Ag	-1.0	-	1.0	PPM	1st year at 25°C	
Operating Temperature Range	T_use	-20	-	+70	°C	Extended Commercial	
		-40	-	+85	°C	Industrial	
Supply Voltage	Vdd	1.71	1.8	1.89	V		
		2.25	2.5	2.75	V		
		2.52	2.8	3.08	V		
		2.97	3.3	3.63	V		
Current Consumption	ldd	_	6.7	7.5	mA	No load condition, f = 20 MHz, Vdd = 2.5 V, 2.8 V or 3.3 V	
	İ	-	6.1	6.7	mA	No load condition, f = 20 MHz, Vdd = 1.8 V	
Standby Current	I_std	_	2.4	4.3	μA	ST = GND, Vdd = 3.3 V, Output is Weakly Pulled Down	
		-	1.2	2.2	μA	ST = GND, Vdd = 2.5 or 2.8 V, Output is Weakly Pulled Do	
	Ì	-	0.4	0.8	μA	ST = GND, Vdd = 1.8 V, Output is Weakly Pulled Down	
Duty Cycle	DC	45	50	55	%	All Vdds. f <= 75 MHz	
		40	50	60	%	All Vdds. f > 75 MHz	
Rise/Fall Time	Tr, Tf	-	1	2	ns	20% - 80% Vdd=2.5V, 2.8V or 3.3V, 15pf load	
		-	1.3	2.5	ns	20% - 80% Vdd=1.8V, 15pf load	
Output Voltage High	VOH	90%	-	-	Vdd	IOH = -4 mA (Vdd = 3.3 V) IOH = -3 mA (Vdd = 2.8 V and Vdd = 2.5 V) IOH = -2 mA (Vdd = 1.8 V)	
Output Voltage Low	VOL	-	-	10%	Vdd	IOL = 4 mA (Vdd = 3.3 V) IOL = 3 mA (Vdd = 2.8 V and Vdd = 2.5 V) IOL = 2 mA (Vdd = 1.8 V)	
Output Load	Ld	-	-	15	pF	At maximum frequency and supply voltage. Contact SiTime higher output load option	
Input Voltage High	VIH	70%	-	-	Vdd	Pin 1, OE or ST	
Input Voltage Low	VIL	-	-	30%	Vdd	Pin 1, OE or ST	
Startup Time	T_osc	-	-	10	ms	Measured from the time Vdd reaches its rated minimum va	
Resume Time	T_resume	-	3.0	4	ms	Measured from the time ST pin crosses 50% threshold	
RMS Period Jitter	T_jitt	-	-	4.0	ps	f = 75 MHz, Vdd = 2.5 V, 2.8 V or 3.3 V	
		-	-	6.5	ps	f = 75 MHz, Vdd = 1.8 V	
RMS Phase Jitter (random)	T_phj	-	0.6	-	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz, VDD = 2.5 V, 2.8 V, or 3.3 V	
		-	0.8	-	ps	f = 75 MHz, Integration bandwidth = 900 kHz to 7.5 MHz, VDD = $1.8$ V	

SiTime quartz replacement electromechanical oscillator

## How do we design one?



General design:

- Find geometry that resonates at desired frequency
- Array devices so impedance (motional resistance) is low so it connects to circuits effectively (RF 50 ohm or good for sustaining amplifier)
- Drive and sense electrostatics
- Reliability: Stress relief
- Package effects
- Frequency stability
  - Effect of temperature, stress, packaging(!) to make compensating circuit?

Phase noise reduction (most challenging for MEMS!):

- High Q (low loss)
  - Vacuum sealed: Thermoelastic damping loss and anchor loss
- Power handling (how high a voltage can I drive it before it goes nonlinear?)

Initial design: What should the shape be? (From SiTime Patent 7227432)



2) United States Patent



Coventor's MEMS+ for design tradeoffs, optimization, electrical-in, electrical-out, and frequency stability



# And how will I array them?



#### For better power handling and lower impedance

All are possible with MEMS+



## **Coupling Beam Length impact on frequency**

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Coventor MEMS+ C.I.m. Coventor MEMS+ C.I.m. ManeraDatabase From ManeraDatabase From Mathematic Correctors Mathematic Correctors Mat	All/support/ResonatorCollateral/Res consistent ↑ provate ♦ consist	<pre>ClimatiNupperNessonatorCollateralisweepCouplingBeamArray.m* Text Go Cd Toob Debug Deskup Window Heb i</pre>	Use M to swe Length modal Also v depen	AEMS+ 2.1 with Matla eep the Coupling Bea h and compute the frequencies view spurious mode adency	ab am
	Coupling Beam Length	100 um	200 um	300 um	
	Frequency	2.28MHz	2.18MHz	2.10MHz	

### **Anchor Placement**





Anchor where resonator doesn't move (nodal points). But it does rotate there.



3.28MHz – much stiffer (was 2.28MHz) and the anchors interfere with the mode (squares are not moving symmetrically)

## Anchor Design



A 'zero impedance' anchor: Choose support beam dimensions so the resonator frequency is its first mode of twist about z

- Doesn't interfere with desired resonator mode
- Reduces stress on anchor, and thus reduces anchor loss



Fig. 3. Schematic of an EWGR support beam, equating it to a beam with simple-fixed boundary conditions.



51 MHz -- 25x too high for this 2MHz resonator

## **Optimum Support Beam**



Quarter wavelength beam and resonance frequency both depend on coupling beam length. Where is optimal length to make the support beam ¼ wavelength of the array's resonance frequency?



## **Zero Impedance Anchor**

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Run single MATLAB script to

- •Specify mode <u>shape</u> of interest
- •Sweep over Coupling Beam Lengths

•Automatically extract mode frequency for mode shape of interest (even if mode number changed)

•Plot



## Frequency Stability with Temperature

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Thermal Expansion

$$\alpha_{TCE} = \frac{1}{L} \frac{\partial L}{\partial T} = 2.5 \times 10^{-6} / K$$

Elastic Modulus temperature dependence

$$E = E_0 (1 + \alpha_{TCF} (T - T_0))$$
$$\alpha_{TCF} = \frac{1}{E} \frac{\partial E}{\partial T} = -52 \times 10^{-6} / K$$

#### Effect of both on frequency:



## **Process Variation Effects on Frequency**

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## **Coupled Mechanical**, **Electrical and IC**

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(simplified for illustration)

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Model is immediately available in Cadence Virtuoso and **Mathworks** Simulink and MATLAB.

No extraction or equivalent circuits to create.

Captures multiple modes.

Parametric

cādence

Fully nonlinear

Electrostatic spring softenting

## **MEMS-IC Electronic Output**

MEMS+ model is still fully parametric and can show output electrical response to input electrical stimulus. Below we see dependence on Temperature and DC Bias

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## **Production Design**



## Coventor's Analyzer tool suite

- Stress Relief
- Loss mechanisms to improve Q
  - Thermoelastic Damping
  - Anchor Loss
- Package Effects

## Exploring designs for Stress Relief

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## Effect of details on mechanics





## Exploring designs for Thermo-elastic Damping





	No Perforations	5u X 40u@Center	3 uniformly distributed 5u Square holes	
Q	26550	33083	26800	
Frequency	2.41MHZ	2.48MHZ	2.42MHz	



What does anchoring do to the mechanical response? Small substrate added below resonator

	Freq	Amplitude At 2.300MHz	Strain Energy Resonator	Strain Energy Substrate (green)	Strain Energy Substrate (red)
No Substrate	2.324MHz	0.265	9.32e5	0	0
Substrate	2.320MHz	0.308	12.9e6	63.1	0.39

Adding the substrate allows anchor to twist slightly which very slightly lowers the resonance frequency, but also allows a higher amplitude of oscillation which improves the strain energy. Note the twisting generates strain directly below the anchor (green block) and little elsewhere in the

ООО "Евроинтех" 2012 substrate

### **Anchor loss**



Magnitude of

displacement

field in

substrate

showing

outgoing

# The small energy present in the larger substrate is the origin of anchor loss



Re(displacement X)

Use absorbing boundary conditions to treat substrate as infinite and compute lost energy

acoustic wave bing boundary to treat substrate as

Q = 74e6 without thermoelastic damping

So thermoelastic damping of 26,000 on previous slides is the dominant damping mechanism! ООО "Евроинтех" 2012

# How do asymmetries affect anchor loss?



Any asymmetries from process or design won't perfectly "twist" the anchor. On the right, we drive it asymmetrically and generate both a compressive and shear wave which lowers Q

#### Symmetric drive



#### Pull and push each square



ООО "Евроинт ex = 2742600,000

Asymmetric drive



Push 1 side only



Q = 863,000

### Package effects





When package warps with temperature, anchor points spread apart or come closer causing stress, which changes frequency (or offsets capacitances)

(Simulations not completed)




Coventor's MEMS+ and Analyzer tools work together to take resonators from initial design ideas to production.

General design:

- Find geometry that resonates at desired frequency
- Array devices so impedance (motional resistance) is low so it connects to circuits effectively (RF 50 ohm or good for sustaining amplifier)
- Drive and sense electrostatics
- Reliability: Stress relief
- Package effects (TO DO)

Frequency stability

• Effect of temperature, stress, packaging(!) to make compensating circuit?

Phase noise reduction (most challenging for MEMS!):

- High Q (low loss)
  - Vacuum sealed: Thermoelastic damping loss and anchor loss
- Power handling (how high a voltage can I drive it before it goes nonlinear?) (TO DO)



## Coventor Solutions for Vibratory Gyroscopes Design and Integration

#### **Applications of Gyroscopes**

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#### Overview



#### Introduction

- Applications of MEMS vibratory gyroscopes
- Typical gyroscope specifications
- Coventor's Value:
  - Design and integration challenges
- An example showing use of Coventor's tools
  - a single-axis gyroscope from the Univ. of British
     Columbia
  - Frequency response and electrostatic spring softening for the matched-mode condition
  - Simulation of sensitivity and cross-axis sensitivity
  - Damping estimation

## Conclusions

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## **Spec sheet for commercial InvenSense IDG-650**

Linear Acceleration Effect

Any axis



Gyroscope specs

that can be simulated with Coventor tools

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PARAMETER	CONDITIONS		MIN	TYP	MAX	UNITS
SENSITIVITY						
Full-Scale Range		±2000		°/s		
	At X4.5OUT and Y4.50	UT		±440		°/s
Constitution				0.5		
Sensitivity	At X-OUT and Y-OUT			0.5		mv/*/s
	At X4.5001 and ¥4.50	01		2.27		mv/*/s
Initial Calibration Tolerance	At X-OUT and Y-OUT			±6		%
Calibration Drift Over Specified Temperature	At X-OUT and Y-OUT			±10		%
Nonlinearity	At X-OUT and Y-OUT,	Best Fit Straight Line		<1		% of FS
Cross-axis Sensitivity		-		±1		%
ZERO-RATE OUTPUT (ZRO)						
Static Output (Bias)	Factory Set			1.35		v
Initial Calibration Tolerance		With Auto Zero		±20		
	Relative to VREF	Without Auto Zoro		+150		mV
ZRO Drift Over Specified Temperature	Highlighted pa	rameters are sho	own in t	he follov	ving slie	des <sup>-</sup>
Power Supply Sensitivity	@ 50 Hz			10		°/sec/V
FREQUENCY RESPONSE						
High Frequency Cutoff	Internal LPF -90°			140		Hz
LPF Phase Delay	10Hz			-4.5		•
MECHANICAL FREQUENCIES						
X-Axis Resonant Frequency			20	24	28	kHz
Y-Axis Resonant Frequency			23	27	31	kHz
Frequency Separation	X and Y Gyroscopes			3		kHz
NOISE PERFORMANCE Total RMS Noise	Bandwidth 1Hz to 1kHz	, At X-OUT and Y-OUT		0.3		mV rms
POWER ON-TIME						
Zero-rate Output	Settling to ±3°/s		50	200	ms	
ULL <sup>1</sup>	1005					
NUII	$-40^{\circ}$ to $\pm 105^{\circ}$		2.2	25 2	78 IV	

0.1

°/sec/g

#### An Example: A single-axis Gyroscope



#### Single proof mass gyroscope fabricated in SOIMUMPs technology

• Thickness: 25 μm, Minimum Gap size: 2 μm

Measure Angular Rare around Z axis



Reference: M.Sharma, E.H.Sarraf, E.Cretu (The Univ. of British Columbia), "Parametric Amplification/Damping in MEMS Gyroscopes", MEMS 2011

## **Coventor MEMS+ for Matlab and Cadence**



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## Electro-Mechanical Modeling in MEMS+





#### **Mechanical Frequencies**

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Initial Design – Drive/Sense modes have a frequency split

• Drive and sense mode frequencies can be compensated by adjusting the DC bias voltage on the sensing or actuation comb drives





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Deformed shapes are exaggerated accordingly

### Parametric Study Q factor vs. Damping Coefficient





Q factors are measured as a ratio of AC to DC amplitudes

Damping Coefficients in actuation and sensing are estimated and assigned to rigid plate (Highlighted in yellow)



Simulated in MATLAB

COVENTOR

### Parametric Study for mode-matched condition



Vary a design parameter, Beam Length in Y, to measure resonant frequency change

Mechanical stimuli are applied



## Next, set the Beam Length = 407 $\mu m$ , and vary Bias Voltage, measure resonant frequency shift



Resonant Frequency change in Drive/Sense-Dir with Bias Voltage

## Sensitivity and Cross-Axis Sensitivity for Capacitive Sensing





Cross-Axis Sensitivity vs. Sidewall Angle

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Other effects such as **misalignment** (In-Plane rotation Angle) or **anisotropic elasticity** can be included

#### **Linear Acceleration Effect**

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Measure linear acceleration stability, Reject external vibrations Sample experimental data below from a source

Apply sinusoidal acceleration (1g) to see acceleration stability over frequency

Capacitance change is observed in y-axis stimulus Gyroscope register an incorrect reading when subjected to a linear acceleration in the same direction as Coriolis force to be sensed.

Simulated in MATLAB Transient Analysis







## Gas Damping Analysis - System Decomposition

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Contributions to x or y-direction gas damping of the gyroscope (Note: other damping mechanisms are likely negligible at low frequencies)

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Total fluidic damping coefficients are x-dir: 1.30e-5 (N/(m/s)) y-dir: 4.36e-5 (N/(m/s))

Slide 13

#### **Cadence Schematic Design**





#### **Non Linear Response**

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V1 = 13.1 + Vac sin(wt)

V2 = 13.1 - Vac sin(wt)

Out of phase voltages on stators resonates proof mass in Y direction

What amplitude of drive, Vac, leads to nonlinear frequency response?

30 DOF system, Q=1600, f0 = 7014 Hz

#### **MEMS+** Matlab integration

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Use FrequencyHysteresis module to compute nonlinear frequency response for

Vac = 1, 1.5, 2, 2.5, 3 Volts



Mechanical nonlinearity 'bends' curve to the right in typical Duffing effect.

Electrostatic nonlinearity would bend curve to left, but since motion is parallel to fingers, electrostatics remained comparatively linear.

Total CPU time to compute these 5 curves: 1100 seconds

#### Conclusions



- <u>Sensitivity</u>
- Cross-axis sensitivity
- Full-scale range and Nonlinearity
- Linear acceleration effect and shock response
- Noise

*MEMS*+ is ideal for design exploration and optimization

- Use CoventorWare to verify MEMS+ results
- Some physics require CoventorWare field solvers
  - Gas damping of comb drives
  - Mechanical details such as filets and anchors



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Filets at connections



## Solution for MEMS Accelerometer Design and Integration

#### Overview



### Introduction

- Applications of MEMS accelerometers
- Typical accelerometer specifications

## Simulation of key accelerometer specs using Coventor tools

- A single-axis accelerometer in IMEC's SiGe process
  - Frequency response and sensitivity of design
  - Damping Analysis
  - Harmonic Analysis
  - Verification with FEA
  - Transient response under a g pulse
  - Simulation of self-test functionality

#### Comparison between simulation and experimental results

#### Applications of MEMS accelerometers

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## Spec sheet single-axis accelerometer (ADXL78)



# Coventor tools can simulate these specs

		Mode	No. Al	022279	Model No. AD22280			Model			
Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
SENSOR											
Output Full-Scale Range	l <sub>ouτ</sub> ≤ ±100 μA	37			55			70			g
Nonlinearity			0.2	2		0.2	2		0.2	2	%
Package Alignment Error			1			1			1		Degree
Cross-Axis Sensitivity		-5		+5	-5		+5	-5		+5	%
Resonant Frequency			24			24			24		kHz
Sensitivity, Ratiometric (Over Temperature)	V <sub>DD</sub> = 5 V, 100 Hz	52.25	55	57.75	36.1	38	39.9	25.65	27	28.35	mV/g
OFFSET											
Zero-g Output Voltage (Over Temperature) <sup>2</sup>	$V_{OUT} - V_{DD}/2,$ $V_{DD} = 5 V$	-200		+200	-150		+150	-150		+150	mV
NOISE											
Noise Density	10 Hz – 400 Hz, 5 V		1.1	3		1.4	3		1.8	3.5	mg/√Hz
Clock Noise			5			5			5		mV p-p
FREQUENCY RESPONSE	2-pole Bessel										
–3 dB Frequency		360	400	440	360	400	440	360	400	440	Hz
-3 dB Frequency Drift	25°C to T <sub>MIN</sub> or T <sub>MAX</sub>		2			2			2		Hz
SELF-TEST											
Output Change (Cube vs. V <sub>DD</sub> ) <sup>3</sup>	$V_{DD} = 5 V$	440	550	660	304	380	456	216	270	324	mV
Logic Input High	$V_{DD} = 5 V$	3.5			3.5			3.5			V
Logic Input Low	$V_{DD} = 5 V$			1			1			1	V
Input Resistance	Pull-down resistor to GND	30	50		30	50		30	50		kΩ
OUTPUT AMPLIFIER											
Output Voltage Swing	l <sub>out</sub> = ±400 μA	0.25		$V_{DD} - 0.25$	0.25		$V_{DD} - 0.25$	0.25		$V_{DD} - 0.25$	V
Capacitive Load Drive		1000			1000			1000			pF
PREFILTER HEADROOM			280			400			560		g
CFSR @ 400 kHz			5			4			3		V/V
POWER SUPPLY (VDD)		4.75		5.25	4.75		5.25	4.75		5.25	V
Functional Range		3.5		6	3.5		6	3.5		6	V
Quiescent Supply Current	$V_{DD} = 5 V$		1.3	2		1.3	2		1.3	2	mA
TEMPERATURE RANGE		-40		+105	-40		+105	-40		+105	°C

## IMEC single-axis accelerometer



#### Process & design data provided for IMEC SiGe process

University reference available, design files available from workshop



Figure 1: Schematic view of the poly-SiGe lateral capacitive accelerometer with self-testing electrodes and shock protectors



Figure 2: Fabrication process flow of the poly-SiGe lateral capacitive accelerometer

Reference: L. Wen, *et al*, "A Comb Based In-Plan Capacitive Accelerometer for Above-IC Integration, U. Leuven and IMEC, Belgium, 2010

## Layout of single-axis accelerometer

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#### **Sensor specs**



	Parameter	Conditions	Min	Тур	Max	Min	Тур	Max	Min	Тур	Max	Unit
	SENSOR											
(	Output Full-Scale Range	l <sub>oυτ</sub> ≤ ±100 μA	37			55			70			g
l	Nonlinearity			0.2	2		0.2	2		0.2	2	%
	Package Alignment Error			1			1			1		Degree
	Cross-Axis Sensitivity		-5		+5	-5		+5	-5		+5	%
$\square$	Resonant Frequency			24			24			24		kHz
	Sensitivity, Ratiometric (Over Temperature)	V <sub>DD</sub> = 5 V, 100 Hz	52.25	55	57.75	36.1	38	39.9	25.65	27	28.35	mV/g

## Resonant frequency modal frequencies and shapes





### **Output Range MEMS+** validated with FEA





Input g Vs Y displacement of proof mass

Input g Vs normalized capacitance of sensing comb fingers

Normalized Capacitance =  $\frac{C_1 - C_2}{\dots}$ 

 $C_1 + C_2$ 

## Fluidic damping analysis: system decomposition



Stokes solver for damping between sense comb fingers



Stokes solver for damping between self test comb fingers

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Key simulation parameters Ambient gas: N<sub>2</sub> Pressure: 1 bar Temperature: 300K

Reynolds solver for slide damping



(Note: other damping mechanisms are likely negligible at low frequencies)

### Fluidic damping analysis: total damping coefficient

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	Damping Coefficient					
	(N/m/s)					
Proof Mass	2.45E-07					
ST Structures	1.83E-07					
Comb Fingers	2.02E-05					
Total	2.06E-05					

## Harmonic analysis with damping



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#### **Transient response under** g pulse

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(-46.3, 112, 7)

5e-10 -5e-10 -1e-09 -1.5e-09 -2e-09

#### MEMS + IC

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Sensitivity:  $\sim 18.5 \text{ mV/g}$  with Vdd = 5V

#### **Self-test specification**



NOISE											
Noise Density	10 Hz – 400 Hz, 5 V		1.1	3		1.4	3		1.8	3.5	mg/√Hz
Clock Noise			5			5			5		mV p-p
FREQUENCY RESPONSE	2-pole Bessel										
-3 dB Frequency		360	400	440	360	400	440	360	400	440	Hz
–3 dB Frequency Drift	25°C to		2			2			2		Hz
	Tmin or Tmax										
SELF-TEST											
Output Change (Cube vs. V <sub>DD</sub> ) <sup>3</sup>	$V_{DD} = 5 V$	440	550	660	304	380	456	216	270	324	mV
Logic Input High	$V_{DD} = 5 V$	3.5			3.5			3.5			V
Logic Input Low	$V_{DD} = 5 V$			1			1			1	V
Input Resistance	Pull-down resistor to GND	30	50		30	50		30	50		kΩ

How much y-displacement due to 5V bias on self-test comb?

 Since we know sensitivity (mV/g) and y-displacement vs. acceleration, this will give us the output change in mV

## Self test : Cadence simulation results

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Y-dir displacement of Proof mass

Voltage on top self test comb is swept from 0 to 5V Zero g is applied on the proof mass

## Simulation and experimental results





The static CV results were plotted and compared. The left figure has both experimental and simulation data, and the right figure shows the difference in terms of percentage number for each voltage point.



## Coventor Solutions for Vibrational Piezoelectric Energy Harvester Design and Integration
### Overview



Introduction

- New applications for MEMS Energy Harvesters
- Energy Harvesting Principles
- Key characteristics
- Design and integration challenges

An example showing use of Coventor's tools

- Energy Harvester and conditioning circuit design
- Validation with measures
- Packaging

Conclusions

3

## **Applications of** miniaturized Energy Harvesters

Powering Distributed Wireless Sensor Nodes

Powering Implanted Sensors for Health Monitoring

Recharging batteries

Monitoring Tire Pressure

\* IDTechEX (England)

"-The Energy Harvesting Market will growto 4.4 billion dollars in 2020 from 650 million dollars in 2010

\* Innovative Research and Products (USA)

"The market will expand 73.6% to 1.254billion dollars in 2014 from 79.5 million dollars in 2009"

Source: Hi-Globe website

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Autonomous wireless temperature sensor Source: Holst center







## **Energy Harvesting Principles**

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## Power sources:

Vibrations Thermal RF waves Light Wind



## Harvesting methods:

Piezoelectric Electromagnetic Electrostatic Thermoelectric Pyroelectric Photovoltaic



Source: Hi-Globe website

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## Vibration Energy Harvesting Efficiency

### Piezoelectric:

Piezoelectric material has its dynamical strain converted into voltage difference

### Electrostatic:

Capacitive harvesting with geometrical variations inducing voltage difference

### **Electromagnetic:**

Inductive behavior thanks to dynamical oscillations of magnets inducing electric current in coils

Type

Equation Maximum Maximum  $\sigma_{v}^{2}k^{2}$ 17.7 mJ/cm 335 mJ/cm<sup>3</sup> Piezoelectric u = 44 mJ/cm<sup>3</sup>  $4 \text{ mJ/cm}^3$ Electrostatic u = u = B $4 \, \mathrm{mJ/cm^3}$ 400 mJ/cm<sup>3</sup> Electromagnetic

Practical

Governing

Source: H. Vocca, NiPS Laboratory, Dipartimento di Fisica, Università degli Studi di Perugia, Italy









Theoretical

## COVENTOR

## Vibration Energy Harvester Specifications

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## Key Characteristics

- Operational frequency range :
  - Depends on application : ambient vibration harvesting => low frequency and broadband or tunable harvester
- Generalized ElectroMechanical Coupling
  - Material and technology choice
- Power density (W/cc)
  - Power to size compromise
- Energy management and storage
  - Different conditioning circuits depending how the energy will be used

## Vibration Energy Harvester **Example Design**

## Cantilever with mass :

Use of the d31 piezoelectric coefficient



## Equivalent Model :

electric mechanic Rm Cm Co R Ri Lm DC/DC  $P_{load, \text{max.}} = \left(\frac{F}{\Gamma}\right)^2 \frac{1}{2R_m} \frac{1}{1 + \sqrt{1 + \omega_m^2 R_m^2 C_0^2}}$  $R_{load,opt.} = \frac{\kappa_m}{\sqrt{1 + \omega^2 R^2 C^2}}$ 

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Design Options

parallel configuration

for use of d33

Electrodes: On sides of piezo layer

for d31 or interdigited combs on top

bimorph or multistack with series or

Piezoelectric stack: Unimorph,

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## Vibration Energy Harvester Simulation Challenges



FEA result is limited to power through a basic passive load

• Basic RLC circuit can be plugged to piezoelectric electrodes

Including diodes or transistors is impossible

 $\Rightarrow$  Circuit simulator is needed for getting the real output power from the energy harvester complete system

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### **Coventor Design Flow**

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## Case Study : Holst Center cantilever VEH



Sputter deposition of Aluminum Nitride on a silicon wafer and glass packaging



Vacuum-packaged piezoelectric vibration energy harvesters: damping contributions and autonomy for a wireless sensor system R Elfrink, M Renaud, T M Kamel, C de Nooijer, M Jambunathan, M Goedbloed, D Hohlfeld, S Matova, V Pop, L Caballero and R van Schaijk J. Micromech. Microeng. **20 june** 2010

*Experimental Validation of Aluminum Nitride Energy Harvester Model with Power Transfer Circuit* S. Matova, D. Hohlfeld, R. van Schaijk, C. J. Welham, S. Rouvillois Eurosensors XXIII conference 2009

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## **Energy Harvesting circuit** design

Piezoelectric Energy Harvester with conditioning circuit optimization 44



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# Verification and refinement





### Packaging





## Advantages for Piezoelectric Energy Harvesters

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## **MEMS+Cadence**

- Optimum load analysis for different conditioning circuit
- Design of the Energy Storage System together with the harvester

### CoventorWare

- Precise design of electrodes
- Stress map

## **Combination:**

- Damping simulations
- Study of packaging effects





## **Coventor solutions for Pressure Sensor Design**



## CoventorWare™ 2012



## Capacitive Pressure Sensor

#### Bottom glass cap



## Back-side etch membrane doping



#### Device



## Passivation metal trace



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## Top glass cap sensing electrode





## DESIGNER<sup>™</sup>: AutoMesher<sup>™</sup>





## Effect of Silicon-Glass Stack

#### Z-displacement T=100 °C

#### Von-Mises stress T=100 °C



## ANALYZER<sup>™</sup>: Capacitance

0-1 atm 25 °C no residual stress bias 5V



## ANALYZER<sup>™</sup>: Zdisplacement

#### 1 atm 25 °C no residual stress bias 5V



## ANALYZER™: Von-Mises Stress

#### 1 atm 25 °C no residual stress bias 5V



## Effect of Residual Stress

*capacitance 0-1 atm 25 °C bias 5V* 

\_

residual stress: oxide100MPa(C); doped silicon 10MPa(C)



## Effect of Residual Stress

Z-displacement 0-1 atm 25 °C bias 5V

– no residual stress

residual stress: oxide 100MPa(C); doped silicon 10MPa(C)







## MemPZR finite element solver

 Stress mapped from mechanical mesh onto PZR mesh





## ANALYSER<sup>™</sup> Keypoints

- Developers of MEMS and Micro-fluidic devices use CoventorWare ANALYZER solvers to simulate the physics required
- ANALYZER incorporates all the physical field solvers necessary to successfully analyze, understand and verify these devices
  - Well-Established Finite Element solvers for mechanics, thermal, electrostatic, piezoresistive and piezoelectric problems
  - MEMS specific finite and boundary elements
  - MEMS specific physics
  - Simulations run in a Job queue
    - Status monitoring
  - Multi-core support
  - 64 bit support
  - Powerful results viewer
  - Many options on rendering, data calculation, macro recorder



## Coventor Solutions for MEMS Capacitive Microphone Design and Integration

### Overview



### Introduction

- Applications of Capactive MEMS Microphones
- A typical product spec and which specs be simulated
- Design and integration challenges
- An example showing use of Coventor's tools
  - Simulation sensitivity
  - Simulation of electro-mechanics
  - MEMS sensitivity noise analysis for SNR spec
  - Design optimisation to minimize noise

## **Applications**

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#### **MEMS** Capacitive Microphones



Source: Yole Development

## Spec sheet for Microphone



#### ADMP404

#### SPECIFICATIONS

 $T_A = 25^{\circ}C$ ,  $V_{DD} = 1.8$  V, unless otherwise noted. All minimum and maximum specifications are guaranteed. Typical specifications are not guaranteed.

Table 1.

#### Microphone specs that can be simulated with Coventor tools



Parameter	Symbol	Tort	t Condi	tions	ommonte				Min	Typ	May	Unit
	Symbol	ies	conun	uons/c	onments				INITI	тур	widx	Unit
Directionality										Omni		
Constituity		14	1- 04 di						41	20	25	dDV
Sensitivity	CNID	IKF	12, 94 at	SPL					-41	-30	-35	dBA
Signal-to-Noise Ratio	SINK									02		
Equivalent Input Noise	EIN			FINI	1 .					32		dBA SPL
Dynamic Range		Derived from EIN and maximum acoustic input								88		aB
Frequency Response		LOW	/ freque	ncy –3	aB point					100		HZ
		Hig	h freque	ency -3	dB point					15		KHZ
	10025	Dev	liation li	mits fro	om flat respo	nse with	in pass	band		-3/+2		dB
Total Harmonic Distortion	THD	105 dB SPL									3	%
Power Supply Rejection Ratio $ PSRR $ 217 Hz, 100 mV p-p square wave superimposed on $V_{DD} = 1.8 V$								70		dB		
Maximum Acoustic Input		Pea	k							120		dB SPL
POWER SUPPLY												
Supply Voltage	VDD								1.5		3.6	V
Supply Current	ls										250	μA
OUTPUT CHARACTERISTICS												
Output Impedance	ZOUT									200		Ω
Output DC Offset										0.8		V
<b>Output Current Limit</b>										90		μA
Capacitive Load Drive	-		1000			1000			1000			pF
PREFILTER HEADROOM				280			400			560		g
CFSR @ 400 kHz				5			4			3		V/V
POWER SUPPLY (VDD)			4.75		5.25	4.75		5.25	4.75		5.25	V
Functional Range			3.5		6	3.5		6	3.5		6	V
Quiescent Supply Current	$V_{DD} = 5 V$			1.3	2		1.3	2		1.3	2	mA
TEMPERATURE RANGE			-40		+105	-40		+105	-40		+105	°C
						-						

## Design and Integration Challenges



Architecture: Multi domain physics

• Mechanics, electrostatics, fluidics & electronics



## Design and Integration Challenges



## Co-simulation of:



#### **Coventor MEMS+** for Cadence Virtuoso





### **MEMS+** Model





## **Sensitivity Simulation**

• Fully coupled simulation between microphone and IC

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#### •Sensitivity,

- •d.c., a.c., transient, noise.
- Monte-Carlo, optimization
  - Enabled by parametric model



## **ElectroMechanical Device Simulation**



 Microphone with perforated back plate using circular and arc shaped flexible plates with pressure loads and electrodes



(Perforation are not shown in the image)

Results of a Modal Analysis with Cadence or Matlab/Simulink

## ElectroMechanical Detailed Design



11


#### ElectroMechanical Detailed Design



- Determine effect backplate stiffness
- Determine effect of non ideal anchor on diaphragm stiffness



#### **MEMS Microphone noise** sources



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### **MEMS Microphone noise** sources

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#### MEMS+ Cavity Model



- The Cavity component is an add-on to all MEMS+ flexible plate models for Microphones
- Models the effect of a fluid trapped in a cavity underneath of above a flexible plate.
- Fluidic connector for the cavity pressure and an optional pressure connector for the external pressure
- The model supports the Cadence noise analysis





#### Flexible Plate Model



- The individual layers of each plate component are modeled by a <u>finite shell element</u> known as MITC (mixed interpolation of tensorial components)
- The approximation of the shell edges is defined by the number of mechanical connectors being used



 The number of mechanical connectors can be set in the parameters of the corresponding plate component





•Fully coupled simulation between microphone and IC

COVENTOR

- •Noise,
- •d.c., a.c., transient
- Monte-Carlo, optimization
  - •Enabled by parametric model



#### Advantages for Microphone simulation



Microphone model from MEMS+

- State of the art flexible plate and cavity model suitable for microphones
  - Mechanical and electrical non-linearity
    - Stress, stress gradient, inertial force, contact
  - Electrode perforations for fringing fields
  - Motion in 6 degrees of freedom
  - Flow compliance, resistance, intertance
  - Parametric
- Leverage 20 man years of model development
  - Physics and simulation performance

Microphone + IC model simulations in Cadence

- Fully coupled simulation between microphone and IC
  - d.c., a.c., transient, **noise**, sensitivity, Monte-Carlo, optimization

Validate, verify design details with FEA/BEM tools



# Coventor Solutions for RF Switch Design and Integration

### **RF MEMS - A Variety of Applications**

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#### **MEMS Switches**

- Transmit/Receive Duplexers (TDD)
- Band/Mode Selection
- Time-Delay for Phased-Arrays
- Antenna Diversity
- Reconfigurable Antennas



#### **MEMS Filters (Resonators)**

- Transmit/Receive Duplexers (FDD)
- Band-Select Filters
- IF Channel Filters
- Image Rejection
- RF Filter Bank
- VCO Stabilization
- Self-Filtering Mixers





#### **MEMS** Varactors

- VCO Tuning
- Variable Matching
- Variable Delay Lines
- Variable Filters



#### **Micromachined Transmission Lines**

- Filters / Diplexers
- Antennas
- Antenna Array Manifolds



#### **MEMS** Inductors

- Oscillator Tank Circuits
- LC Filters
- Bias & Matching Circuits



#### **Challenges of RF MEMS**

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#### **Specialized Physics**

- 3D electrostatics
- Electro-mechanical coupling
- Energy loss mechanisms
- Piezoelectric, magnetic,...
- Residual stresses
- Contact forces
- Sticking

**Integration Challenges** 

- Different processes
- Different packaging
- MEMS co-design with IC and RF
- Different design tools



**Coventor's Mission:** Replace *build & test* with simulation

#### **Example: RF MEMS Switch**

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IC designers and system architects require a MEMS device block for their schematic-based simulation environment of choice





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# **MEMS+ with Cadence**

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#### CoventorWare: Coupled Electro-Mech. Field Solver



BEM solver for electrostatic force due to bias voltage -- uses surface mesh



FEM solver for solid mechanics displacement

-- uses volume mesh

#### MEMS + Innovator (3D Design Entry)

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# **MEMS+ Innovator**





## **MEMS+ model in Cadence**







System MEMS / IC co-simulation

# Results in MEMS+ Pull-in Voltage





# Results in MEMS+: Switching time









# MEMS and System Design: MEMS+ for Matlab/ Simulink

Chris Welham Application Engineering Manager Coventor Paris



### Outline

- MEMS+System and IC Challenge
- The MEMS + approach
- Accelerometer example in Simulink
- Using Matlab scripting
- Conclusions



# Coventor MEMS+ for Matlab Simulink





# Accelerometer Design Example

#### Single-axis accelerometer

- Differential capacitance
- Made with DRIE on SOI





#### Sigma-delta modulator

- 2nd order--> good stability
- Provides control & ADC
- Increases dynamic range and sensitivity





# Define Materials and Process

 Material and process properties can be specified as constants, variables, or algebraic expressions

#### **MEMS+ Material Database**

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#### MEMS+ Process Database

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Temperature "T" is defined as a variable then linked to material properties



 The MEMS device models are created with a library of parametric component generators for suspensions, plates, combs and electrical pads





 MEMS system design completed with addition of sigma-delta control loop using models from the Simulink library



#### Concept:

Use controller to hold proof mass steady for any acceleration, and use feedback control signal as output.

# Force-feedback control of accelerometer



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# Stability Simulations in Simulink





# Stability Simulations in Simulink

Could do FFT of bitstream and attempt to interpret....

1-DOF model in MEMS+

Instead, load into *MEMS*+ to visually observe device behavior:



1-DOF model erroneously considers

1-DOF model erroneously considers the system stable ООО "Евроинтех" 2012



Controller excites suspensions into flapping uncontrollably

#### Multi-DoF model MEMS+



## **Component Design**



#### **Design Tradeoff: Sensitivity vs. Linearity**



- Nonlinearities from mechanics and comb electrostatics
- Parameter sweeps computed in seconds



## **Component Design**



#### **Design Tradeoff: Sensitivity for Bandwidth:**



• Not just mechanics or electrostatics: Whole system characteristic

## System performance tradeoffs







### **Package Deformation**

Package deforms due varying ambient temperature

- Deformation causes zero-*g* offset
- Can only predict zero-g offset with multi-DOF model
- Can the effect be minimized?







# Design optimization using MATLAB and MEMS+





# MEMS+-Matlab Interface (no Simulink)

- Drive MEMS+ from MATLAB
- 1. Open MEMS+ 3D schematic
- 2. Creating an instance of the analysis object: DC, AC, Modal
- 3. Setting the desired inputs
- 4. Calling compute() on object
- 5. Extract result data from object

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24		%% load matrices of wafer data (C Youngs and Cpoly thick)
25	-	load WaferMaps.mat
26		
27		8% Compute device performance
28	-	MemsplusSystem('new','GyroscopeCapOutputs_WaferMap.3dsch');
29		<pre>%% get the nominal variable values</pre>
30	-	<pre>vars = vars2map(MemsplusSystem('getVariables'));</pre>
31	-	<pre>Epoly = vars('Epoly');</pre>
32	-	<pre>poly_thickness = vars('poly_thickness');</pre>
33		
34		%% initialize a Wafer map of resonant frequencies
35	-	C_freqsHzDrive = zeros(size(Cpoly_thick));
36	-	C_freqsHzSense = zeros(size(Cpoly_thick));
37		
38		<pre>% previously computed DC soln</pre>
39	-	load someInputs.mat
40		
41		%% Loop over process data
42	-	<pre>for k=1:length(Cpoly_thick(:))</pre>
43	7	<pre>vars('Epoly') = Epoly*(1 + C_Youngs(k)/100);</pre>
44	T	<pre>vars('poly_thickness') = poly_thickness*(1 + Cpoly_thick(k)/100);</pre>
45	-	<pre>Memsplus5ystem('setVariables', map2vars(vars));</pre>
46	-	<pre>abcd = MemsplusSystem('getSystemLinearization',0,states60,inputs);</pre>
47	1 and	[shapes, freqsHz] = computeModesSimple(abcd);
40	1	C_ireqsHzDrive(k) = freqsHz(1);
49	Ē	C_IreqsHzsense(K) = IreqsHz(Z);
50		<pre>% if (mod(k,20) == 1) % print k every 20 steps</pre>
51	-	disp(K);
52		vena
53	-	end

# MEMS+-Matlab Interface (no Simulink)



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Matlab script



#### Sense Frequency



Drive Frequency ООО "Евроинтех" 2012
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# MEMS+-Matlab Interface (no Simulink)



# Vary suspension width and plot response





# Enable MEMS Eco-System

 MEMS + parametric design format provides a new standard to facilitate the communication between the partners of the MEMS eco-system







#### MEMS device and ASIC Integration: MEMS+ for Cadence

**Chris Welham** 

**Application Engineering Manager** 

**Coventor Paris** 









### MEMS and ASIC Integration, Optimization issues: MEMS+ for Cadence Virtuoso

Chris Welham Application Engineering Manager Coventor Paris

#### COVENTOR

### Coventor MEMS+ for Cadence Virtuoso





#### Design and Integration Solutions

#### **Coventor's Value**

## MEMS Multi-Physics: mechanical + electrostatic + IC

- With complex geometry
- With Linear and non-linearity coupled physics



#### COVENTOR esign and Integration Challenges

#### **Coventor's Value**

• Speed vs accuracy



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Accuracy



#### Cadence Virtuoso Cell Generation

 The 3D Innovator design is imported into the Cadence Library Manager using the MEMS+ import tool

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### Parametric Cell Views

 The *MEMS* + import tool automatically creates a parametric layout and schematic view







#### Virtuoso Cell Parameters

 The created cell views features all parameters that were exposed in *MEMS*+

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#### MEMS Device Schematic

 The MEMS designer adds sources to the exposed electrical pins and confirms the device performance running DC, AC and transient simulations





#### MEMS Device Simulation

 Simulation results can be loaded back into *MEMS* + and animated in the 3-D canvas





#### SRAM Memory Cell Design

• The IC designer, meanwhile, creates a schematic of the SRAM memory cell underneath each mirror...





### **Complete Pixel Cell**

 The CMOS SRAM cell can in turn be connected to the mirror to assemble the complete pixel cell





### Mirror Array Schematic

 The pixel cell is replicated to form an array and connected to the driving electronics



Hierarchical symbol of a DMD mirror with memory cell

#### Cadence Virtuoso schematic of memory cell





## Mirror Array Simulation

 The complete mirror array can now be simulated with the Virtuoso simulators: Spectre, UltraSim or APS





# Accelerometer with ΣΔ Feedback Loop

 MEMS + generated accelerometer model with ΣΔ force feedback loop in Cadence Spectre:
Plate Displacement





#### Conclusions

#### MEMS+

- Device design via state-of-the-art non-linear FEA models
  - Electrostatics
  - Mechanical and electrical non-linearity
    - Stress, stress gradient, inertial force, contact
  - Motion in 6 degrees of freedom
  - Parametric
- Access 30 man years of model development
  - Physics *and* simulation performance
- Cadence available for gate level simulations
- Leverage all the benefits of Matlab & Simulink for system level design
  - Toolboxes
  - Scripting